

*B1*

*C1*

*Sub F1*

*F*

1. (Amended) A method for manufacturing a semiconductor device comprising the steps of:  
forming a semiconductor film comprising amorphous silicon over a substrate;  
crystallizing said semiconductor film by irradiating a laser light; forming an insulating film on the crystallized semiconductor film by a vapor phase deposition; and  
irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas.

2. (Amended) The method of claim 1 wherein said intense light is an IR light.
3. (Amended) The method of claim 1 wherein said vapor phase deposition is performed by a plasma CVD or a low pressured CVD.
4. (Amended) The method of claim 1 wherein the irradiation of said intense light is performed in order to reduce an interfacial layer density to  $10^{11} \text{ cm}^{-2}$  or lower.

*B2*

*Sub C2*

6. (Amended) A method for manufacturing a semiconductor device comprising the steps of:  
forming a semiconductor film comprising amorphous silicon over a substrate;  
crystallizing said semiconductor film by irradiating a laser light;  
forming an insulating film comprising silicon oxide on the crystallized semiconductor film by a vapor phase deposition; and

*B2*  
*Concl'd.*

irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas.

*Sub F17*

7. (Amended) The method of claim 6 wherein said intense light is an IR light.

8. (Amended) The method of claim 6 wherein said vapor phase deposition is performed by a plasma CVD or a low pressured CVD.

9. (Amended) The method of claim 6 wherein the irradiation of said intense light is performed in order to reduce an interfacial layer density to  $10^{11} \text{ cm}^{-2}$  or lower.

*B3*  
*Sub C3*

11. (Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon over a substrate;

crystallizing said semiconductor film by irradiating a laser light;

forming an insulating film comprising silicon oxide on the crystallized semiconductor film by a vapor phase deposition using TEOS; and

irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas.

*Sub F17*

12. (Amended) The method of claim 11 wherein said intense light is an IR light.

*B3* *Sub F17* 13. (Amended) The method of claim 11 wherein said vapor phase deposition is performed by a plasma CVD or a low pressured CVD.

Please add new claims 29-37 as follows:

*B4* *Sub F17* --29. The method of claim 11 wherein said the irradiation of said intense light is performed in order to reduce an interfacial layer density to  $10^{11} \text{ cm}^{-2}$  or lower.

*Sub C4* 30. A method for manufacturing a semiconductor device comprising the steps of: forming a crystalline semiconductor film over a substrate; forming an insulating film comprising silicon oxide on said crystalline semiconductor film by a vapor phase deposition; and irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas.

31. The method of claim 30 wherein said intense light is an IR light.

*Sub F17* 32. The method of claim 30 wherein said vapor phase deposition is performed by a plasma CVD or a low pressured CVD.

33. The method of claim 30 wherein the irradiation of said intense light is performed in order to reduce an interfacial layer density to  $10^{11} \text{ cm}^{-2}$  or lower.

*Sub C6* 34. A method for manufacturing a semiconductor device comprising the steps of: forming a crystalline semiconductor film over a substrate;